



DMN3060LWQ

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
001/	60mΩ @ V _{GS} = 10V	2.6A
30V	$100m\Omega @ V_{GS} = 4.5V$	2.1A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN3060LWQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

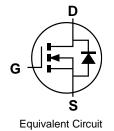
https://www.diodes.com/guality/product-definitions/

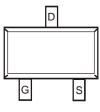
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 🕄
- Weight: 0.027 grams (Approximate)



Top View





Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3060LWQ-7	SOT323	3,000/Tape & Reel
DMN3060LWQ-13	SOT323	10,000/Tape & Reel

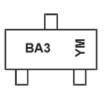
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BA3 = Product Type Marking Code YM or \overline{Y} M= Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н		J	K	L	М	Ν	0	Р	R	S
					1				-			-
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	30	V	
Gate-Source Voltage		Vgss	±12	V
Continuous Drain Current (Note 6) V_{GS} = 10V	ID	2.6 2.1	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	18	A	
Maximum Body Diode Forward Current (Note 5)		ls	0.68	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	251	°C/W
Total Power Dissipation (Note 6)		PD	0.64	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	195	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

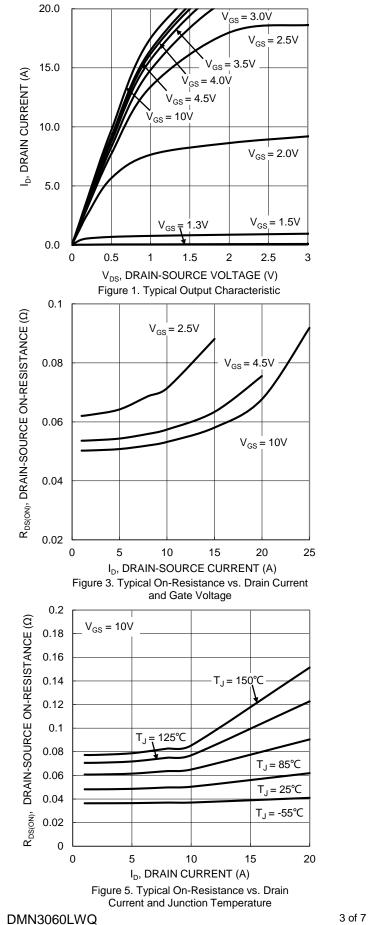
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			0			1	1
Drain-Source Breakdown Voltage		BVDSS	30	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	@Tc = +25°C	IDSS		_	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage		lgss		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		V _{GS(TH)}	0.7		1.8	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance			_	48	60	mΩ	V _{GS} = 10V, I _D = 3.1A
Static Drain-Source On-Resistance		RDS(ON)	_	51	100	11122	V _{GS} = 4.5V, I _D = 2A
Diode Forward Voltage		Vsd	_	0.8	1.2	V	$V_{GS} = 0V$, $I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		Ciss	_	395	_	pF	
Output Capacitance	Output Capacitance			39		pF	Vps = 15V, Vgs = 0V, f = 1.2MHz
Reverse Transfer Capacitance		Crss	_	26	—	pF	T = T.ZIVITIZ
Gate Resistance		Rg	_	3.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge		Qg		5.6	_	nC	
Gate-Source Charge		Qgs	_	0.2	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6A
Gate-Drain Charge		Q _{gd}		1.8	_	nC	ID = 6A
Turn-On Delay Time		td(on)		5.8	_	ns	
Turn-On Rise Time		t _R		30.8	_	ns	$V_{DD} = 10V, V_{GS} = 15V,$
Turn-Off Delay Time		td(OFF)		18.3	_	ns	$R_L = 4.7\Omega, R_G = 3\Omega$
Turn-Off Fall Time		tF	_	2.7	—	ns	

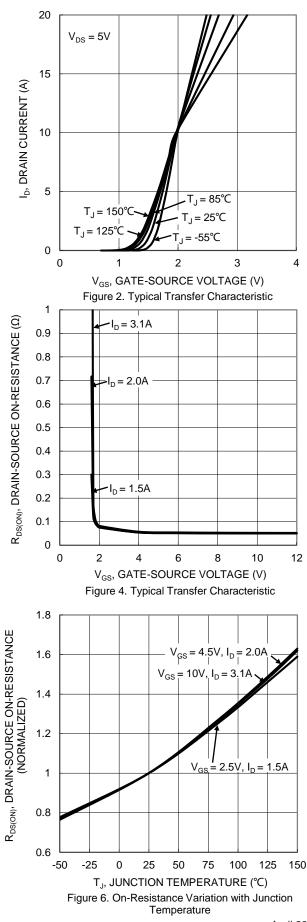
Notes:

Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



DMN3060LWQ



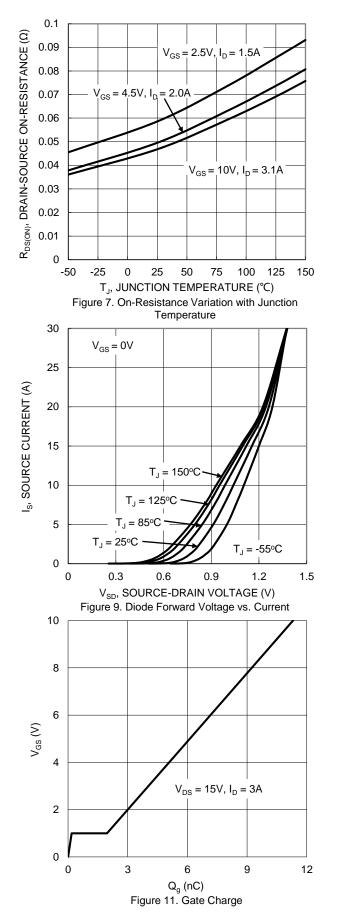


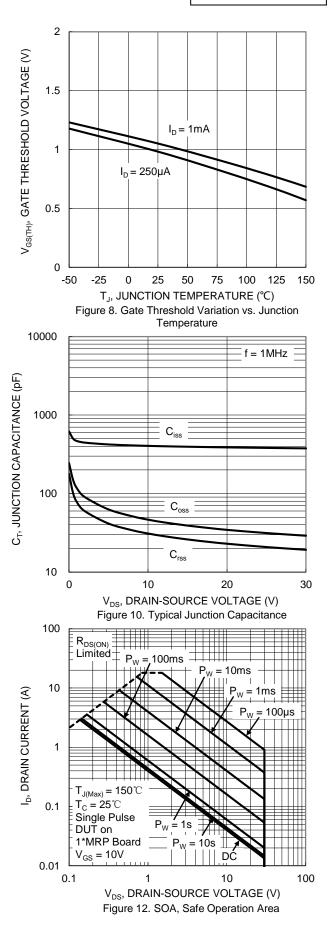
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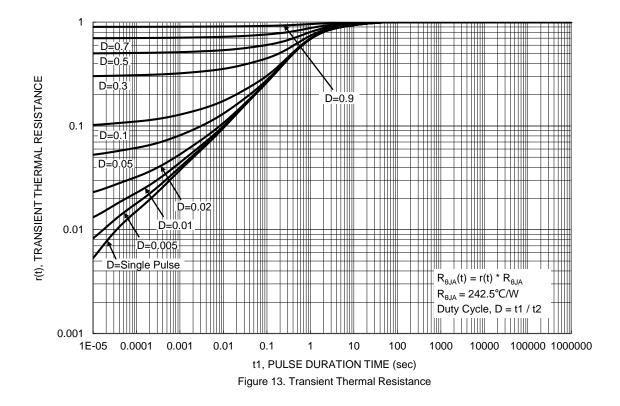
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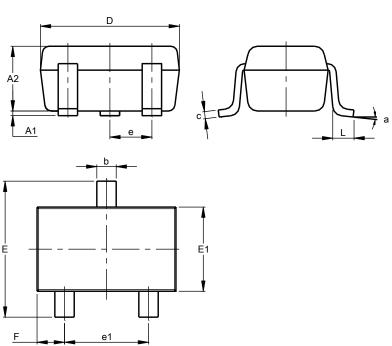




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

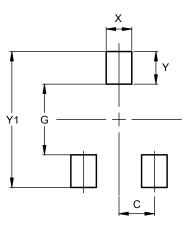
SOT323



SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
c	0.10	0.18	0.11					
D	1.80	2.20	2.15					
ш	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	Dimen	sions i	in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Ŷ	0.600
Y1	2.500

SOT323



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